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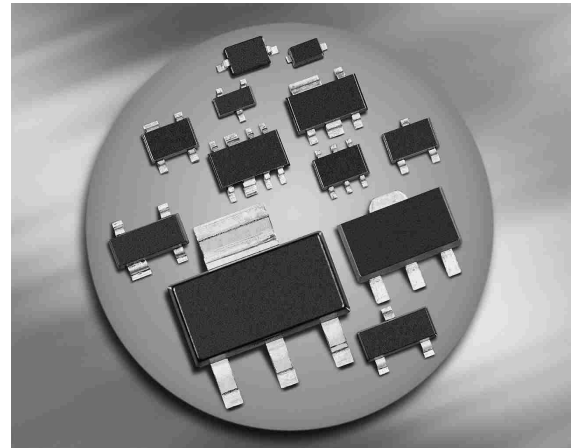
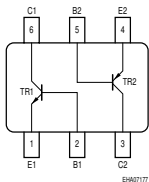
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NPN / PNP Silicon Switching Transistor Array

- High current gain
- Low collector-emitter saturation voltage
- Two (galvanic) internal isolated NPN / PNP transistor in one package
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101


SMBT3904PN
SMBT3904UPN


Type	Marking	Pin Configuration						Package
		1=E	2=B	3=C	4=E	5=B	6=C	
SMBT3904PN	s3P	1=E	2=B	3=C	4=E	5=B	6=C	SOT363
SMBT3904UPN	s3P	1=E	2=B	3=C	4=E	5=B	6=C	SC74

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}	40	V
Collector-base voltage	V_{CBO}	40	
Emitter-base voltage	V_{EBO}	6	
Collector current	I_C	200	mA
Total power dissipation-	P_{tot}		mW
$T_S \leq 115\text{ °C}$, SMBT3904PN		250	
$T_S \leq 105\text{ °C}$, SMBT3904UPN		330	
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R_{thJS}		K/W
SMBT3904PN		≤ 140	
SMBT3904UPN		≤ 135	

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

DC Characteristics

Collector-emitter breakdown voltage $I_C = 1 \text{ mA}, I_B = 0$	$V_{(BR)CEO}$	40	-	-	V
Collector-base breakdown voltage $I_C = 10 \mu\text{A}, I_E = 0$	$V_{(BR)CBO}$	40	-	-	
Emitter-base breakdown voltage $I_E = 10 \mu\text{A}, I_C = 0$	$V_{(BR)EBO}$	6	-	-	
Collector-base cutoff current $V_{CB} = 30 \text{ V}, I_E = 0$	I_{CBO}	-	-	50	nA
DC current gain ²⁾ $I_C = 100 \mu\text{A}, V_{CE} = 1 \text{ V}$ $I_C = 1 \text{ mA}, V_{CE} = 1 \text{ V}$ $I_C = 10 \text{ mA}, V_{CE} = 1 \text{ V}$ $I_C = 50 \text{ mA}, V_{CE} = 1 \text{ V}$ $I_C = 100 \text{ mA}, V_{CE} = 1 \text{ V}$	h_{FE}	40 70 100 60 30	- - - - -	- - 300 - -	-
Collector-emitter saturation voltage ²⁾ $I_C = 10 \text{ mA}, I_B = 1 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 5 \text{ mA}$	V_{CEsat}	- -	- -	0.25 0.4	V
Base emitter saturation voltage ²⁾ $I_C = 10 \text{ mA}, I_B = 1 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 5 \text{ mA}$	V_{BEsat}	0.65 -	- -	0.85 0.95	

¹⁾For calculation of R_{thJA} please refer to Application Note AN077 (Thermal Resistance Calculation)

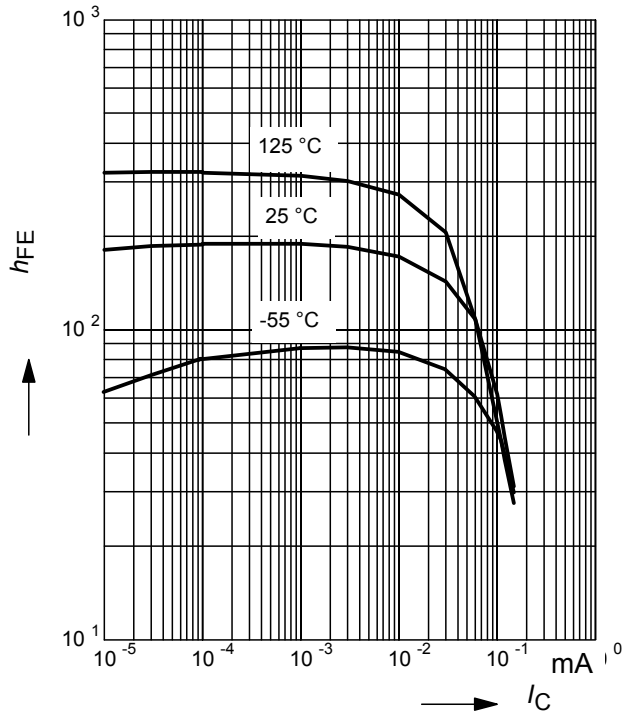
²⁾Pulse test: $t < 300\mu\text{s}$; $D < 2\%$

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics					
Transition frequency $I_C = 10\text{ mA}$, $V_{CE} = 5\text{ V}$, $f = 100\text{ MHz}$	f_T	250	-	-	MHz
Collector-base capacitance $V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{cb}	-	-	3.5	pF
Emitter-base capacitance $V_{EB} = 0.5\text{ V}$, $f = 1\text{ MHz}$	C_{eb}	-	-	10	
Delay time $V_{CC} = 3\text{ V}$, $I_C = 10\text{ mA}$, $I_{B1} = 1\text{ mA}$, $V_{BE(\text{off})} = 0.5\text{ V}$	t_d	-	-	35	ns
Rise time $V_{CC} = 3\text{ V}$, $I_C = 10\text{ mA}$, $I_{B1} = 1\text{ mA}$, $V_{BE(\text{off})} = 0.5\text{ V}$	t_r	-	-	35	
Storage time $V_{CC} = 3\text{ V}$, $I_C = 10\text{ mA}$, $I_{B1} = I_{B2} = 1\text{ mA}$	t_{stg}	-	-	225	
Fall time $V_{CC} = 3\text{ V}$, $I_C = 10\text{ mA}$, $I_{B1} = I_{B2} = 1\text{ mA}$	t_f	-	-	75	
Noise figure $I_C = 100\text{ }\mu\text{A}$, $V_{CE} = 5\text{ V}$, $f = 1\text{ kHz}$, $\Delta f = 200\text{ Hz}$, $R_S = 1\text{ k}\Omega$	F	-	-	5	dB

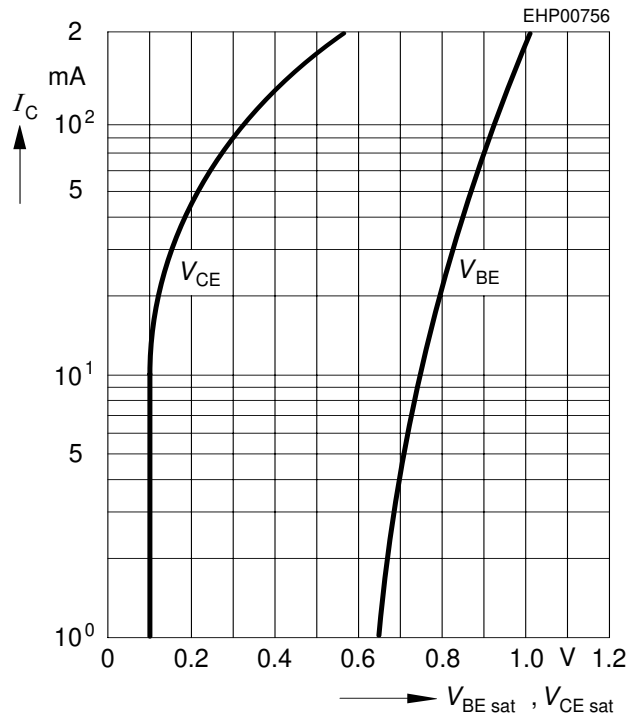
DC current gain $h_{FE} = f(I_C)$

$V_{CE} = 1\text{ V}$, normalized



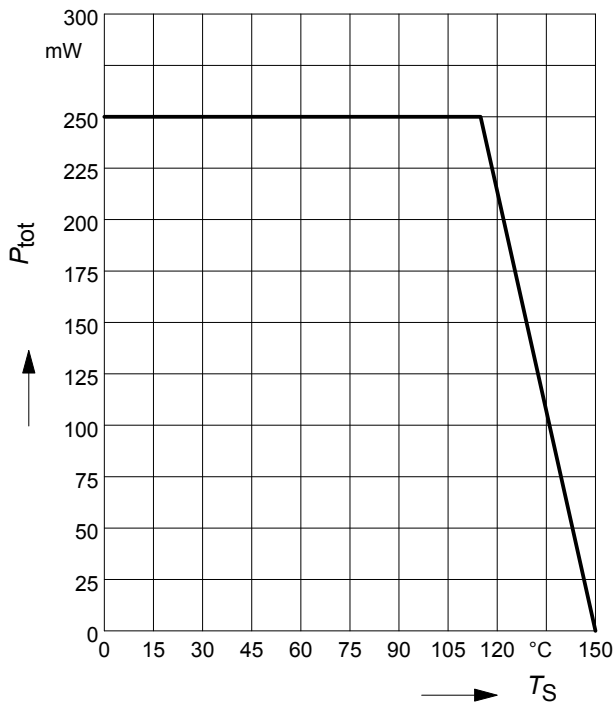
Saturation voltage $I_C = f(V_{BEsat}; V_{CEsat})$

$h_{FE} = 10$



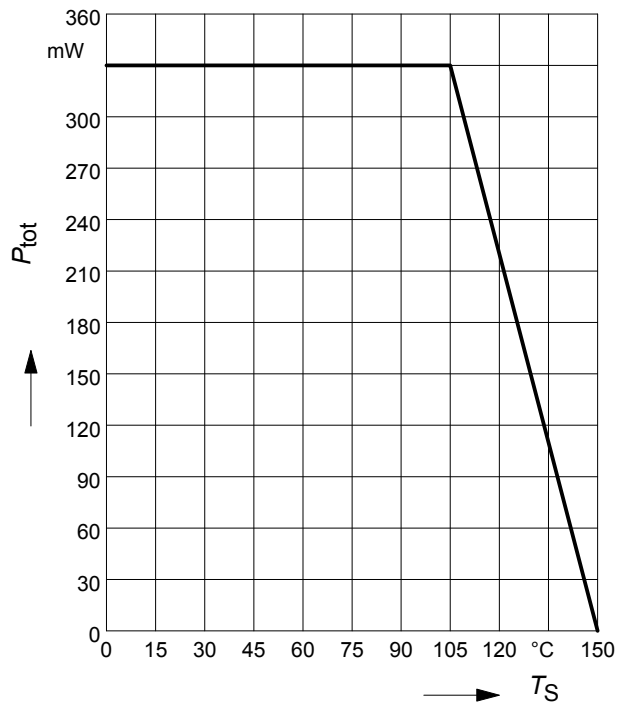
Total power dissipation $P_{tot} = f(T_S)$

SMBT3904PN



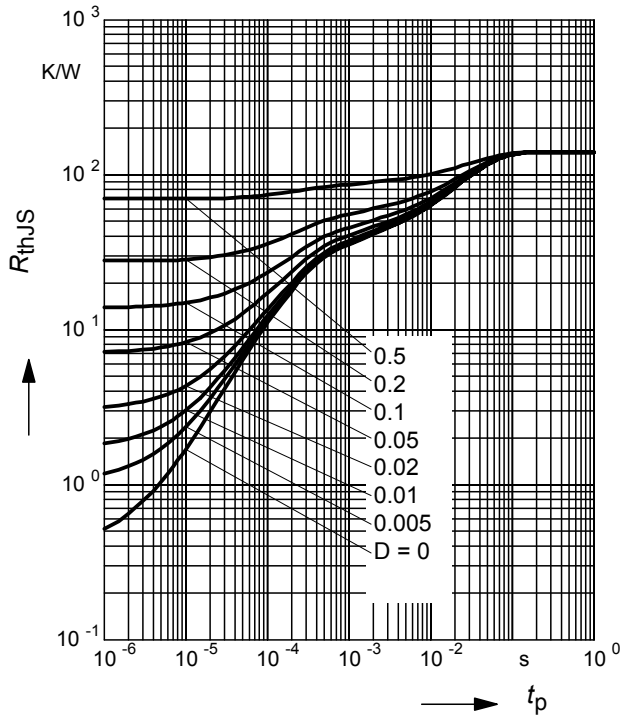
Total power dissipation $P_{tot} = f(T_S)$

SMBT3904UPN



Permissible Pulse Load $R_{thJS} = f(t_p)$

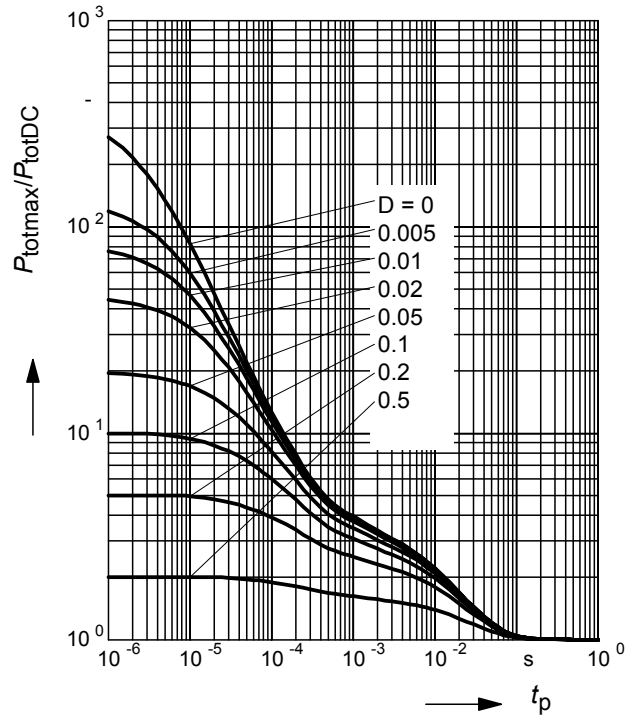
SMBT3904PN



Permissible Pulse Load

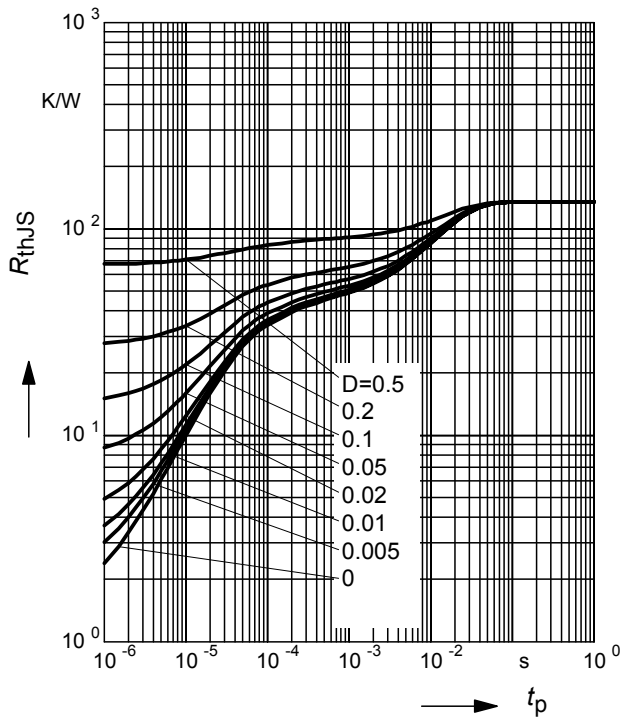
$P_{totmax}/P_{totDC} = f(t_p)$

SMBT3904PN



Permissible Puls Load $R_{thJS} = f(t_p)$

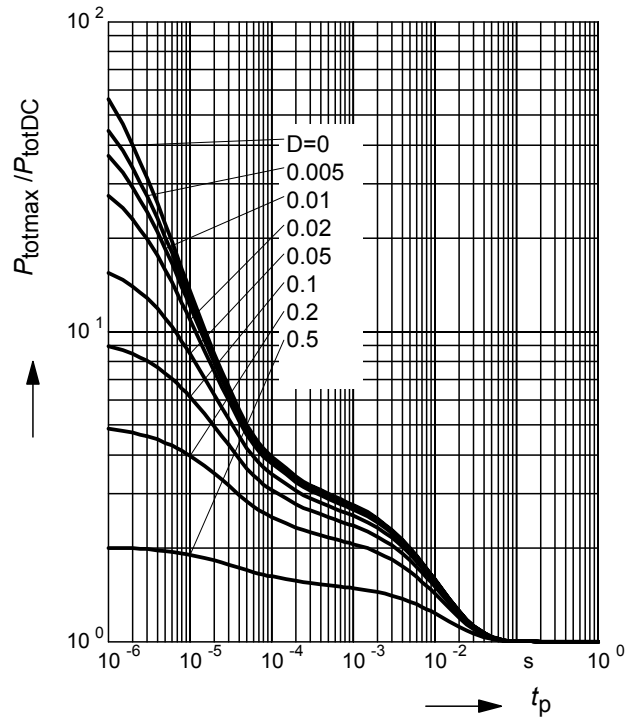
SMBT3904UPN



Permissible Pulse Load

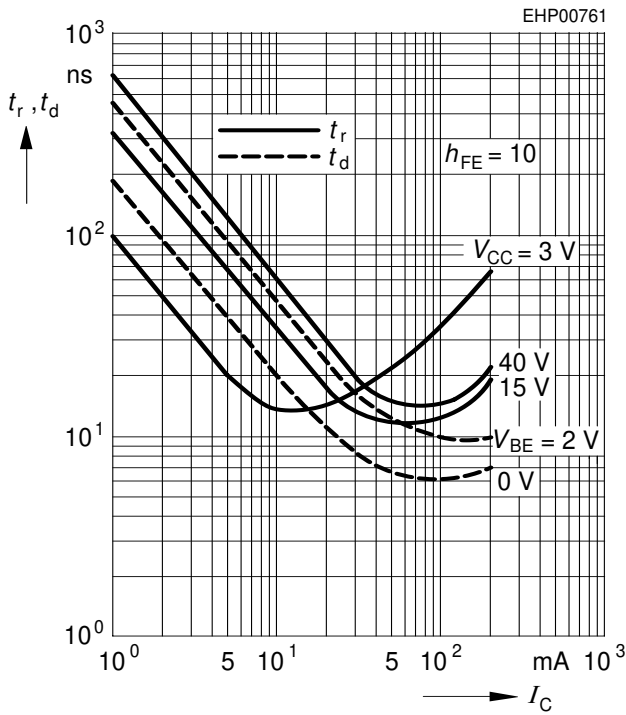
$P_{totmax}/P_{totDC} = f(t_p)$

SMBT3904UPN

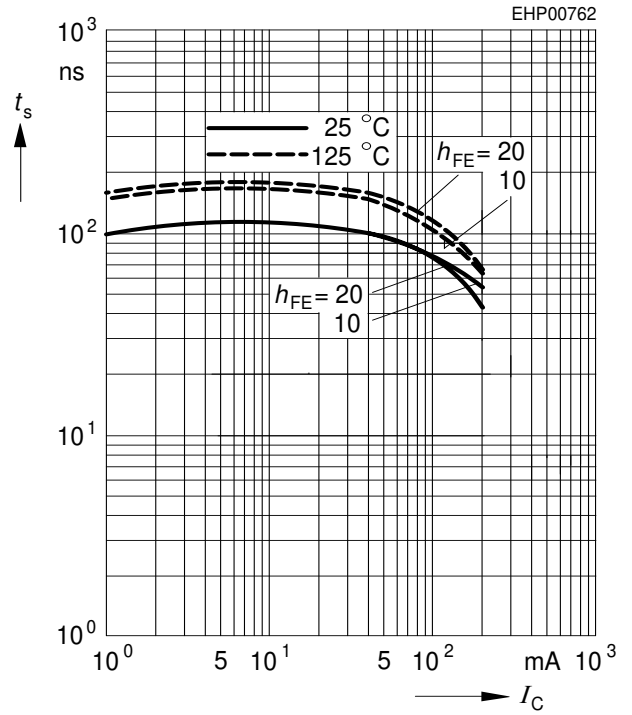


Delay time $t_d = f(I_C)$

Rise time $t_r = f(I_C)$

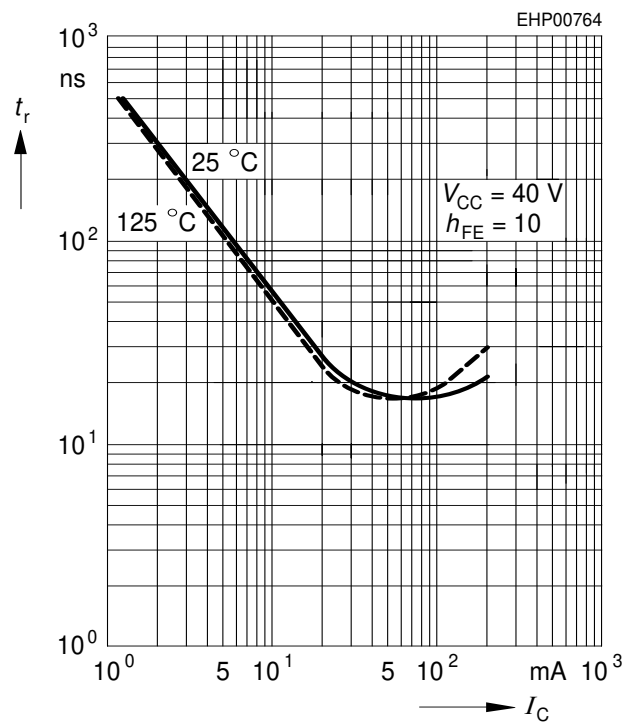
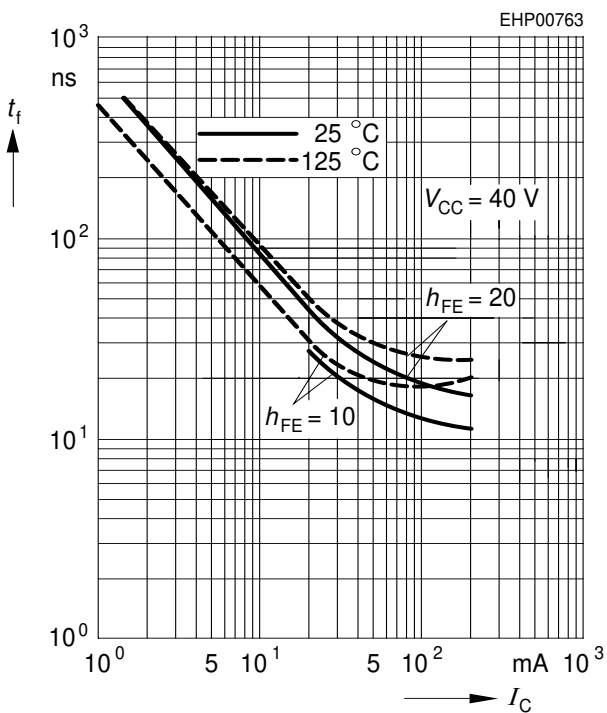


Storage time $t_{stg} = f(I_C)$

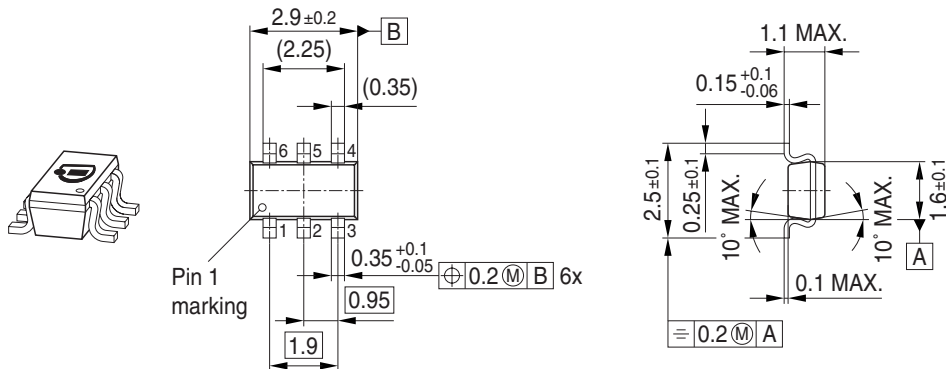


Fall time $t_f = f(I_C)$

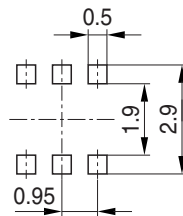
Rise time $t_r = f(I_C)$



Package Outline

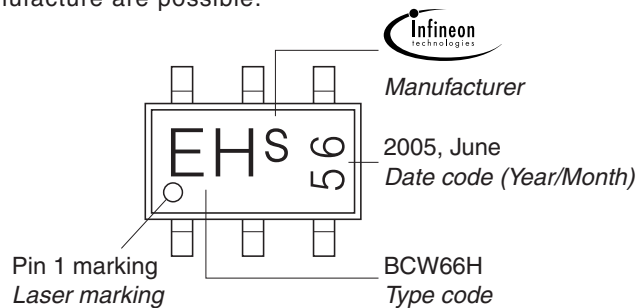


Foot Print



Marking Layout (Example)

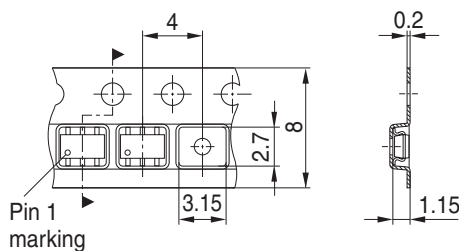
Small variations in positioning of Date code, Type code and Manufacture are possible.



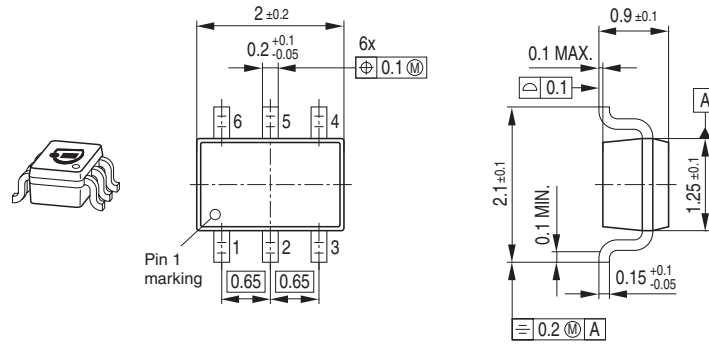
Standard Packing

Reel \varnothing 180 mm = 3.000 Pieces/Reel
 Reel \varnothing 330 mm = 10.000 Pieces/Reel

For symmetric types no defined Pin 1 orientation in reel.



Package Outline

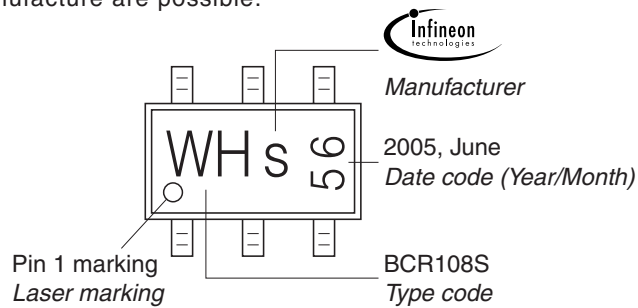


Foot Print



Marking Layout (Example)

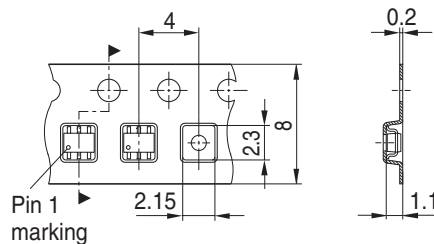
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Standard Packing

Reel \varnothing 180 mm = 3.000 Pieces/Reel
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For symmetric types no defined Pin 1 orientation in reel.



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